

Eudyna GaN-HEMT 180W

EGN21A180IV

Preliminary

High Voltage - High Power GaN-HEMT

FEATURES

- High Voltage Operation : $V_{DS}=50V$
- High Gain: 15dB(typ.) at $P_{out}=45dBm(Avg.)$
- High Efficiency: 32%(typ.) at $P_{out}=45dBm(Avg.)$
- Broad Frequency Range : 2100 to 2200MHz
- Proven Reliability

DESCRIPTION

The EGN21A180IV is a 180 Watt GaN-HEMT that offers high efficiency, high gain, ease of matching, greater consistency and broad bandwidth for high power L-band amplifiers with 50V operation. This device is targeted for high voltage, low current operation in digitally modulated base station applications - ideally suited for W-CDMA base station amplifiers and other HPA designs while offering ease of use.



ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		120	V
Gate-Source Voltage	V_{GS}	$T_c=25^\circ C$	-5	V
Total Power Dissipation	P_t		321	W
Storage Temperature	T_{stg}		-65 to +175	°C
Channel Temperature	T_{ch}		250	°C

RECOMMENDED OPERATING CONDITION(Case Temperature $T_c= 25^\circ C$)

Item	Symbol	Condition	Limit	Unit
DC Input Voltage	V_{DS}		50	V
Forward Gate Current	I_{GF}	$R_G=2 \Omega$	<38.8	mA
Reverse Gate Current	I_{GR}	$R_G=2 \Omega$	>-14.4	mA
Channel Temperature	T_{ch}		200	°C

ELECTRICAL CHARACTERISTICS (Case Temperature $T_c=25^\circ C$)

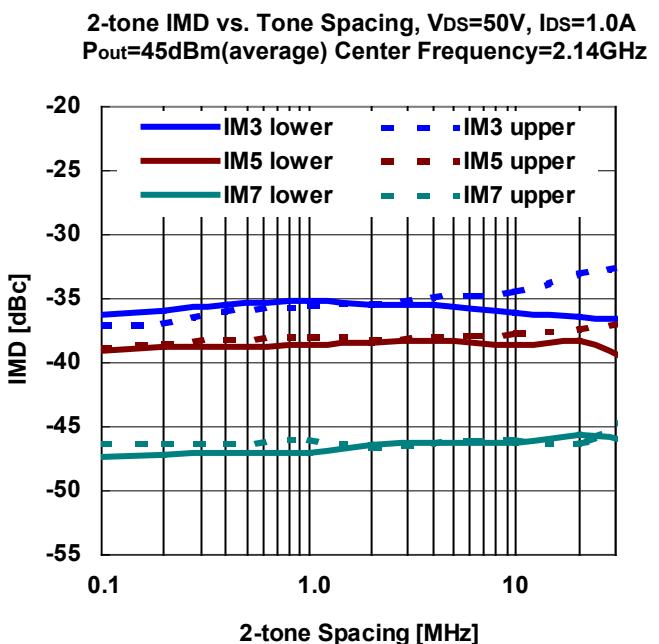
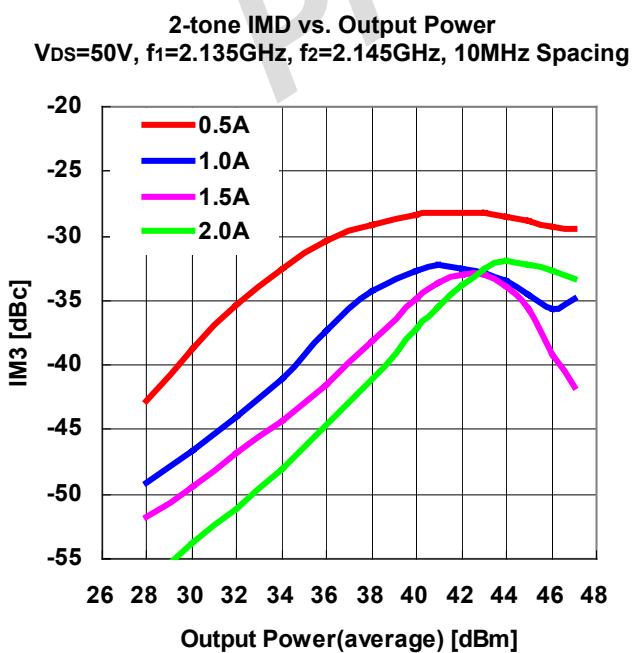
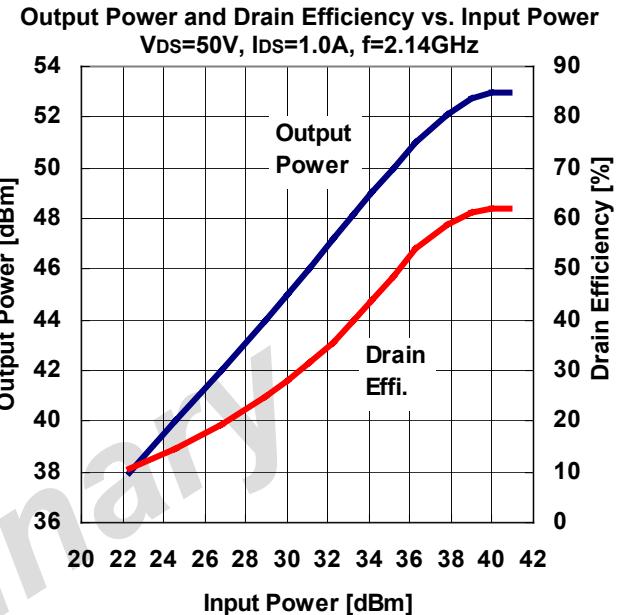
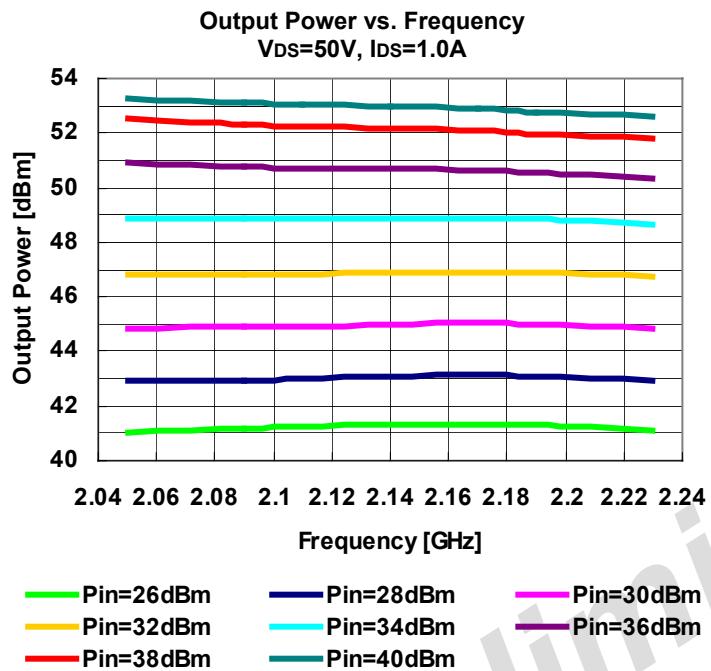
Item	Symbol	Condition	Limit			Unit
			Min.	Typ.	Max.	
Pinch-Off Voltage	V_p	$V_{DS}=50V$ $I_{DS}=72mA$	-1.0	-2.0	-3.5	V
Gate-Drain Breakdown Voltage	V_{GDO}	$I_{GS}=-36 mA$	-	-350	-	V
3rd Order Inter modulation Distortion	IM_3	$V_{DS}=50V$	-	-32	-	dBc
Power Gain	G_p	$I_{DS}(DC)=1.0A$	14.0	15.0	-	dB
Drain Efficiency	η_d	$P_{out}=45dBm(Avg.)$ Note 1	-	32	-	%
Thermal Resistance	R_{th}	Channel to Case	-	0.55	0.7	°C/W

Note 1 : IM3 and Gain test condition as follows:

IM3 & Gain : $f_o=2.135GHz$, $f_1=2.145GHz$ W-CDMA(3GPP3.4 12-00) BS-1 64ch
67% clipping modulation(Peak/Avg. = 8.5dB@0.01% Probability(CCDF)) measured over 3.84MHz at f_o -10MHz and f_1 +10MHz.

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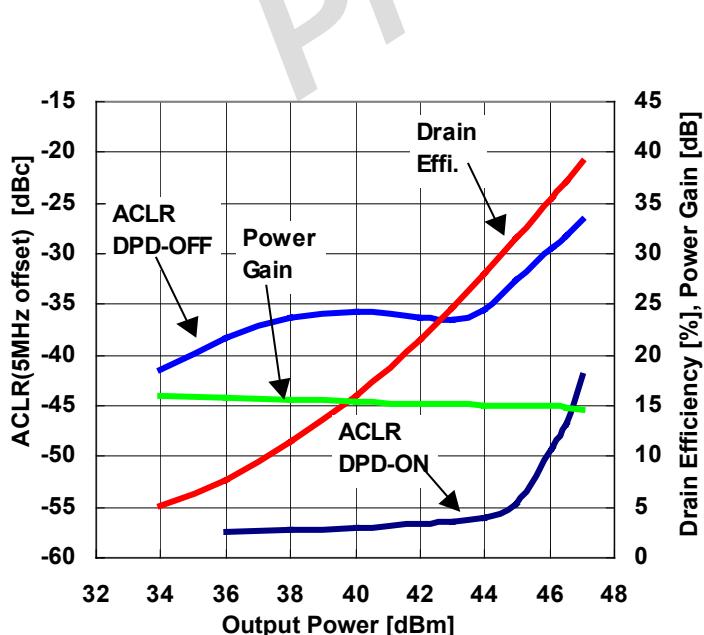
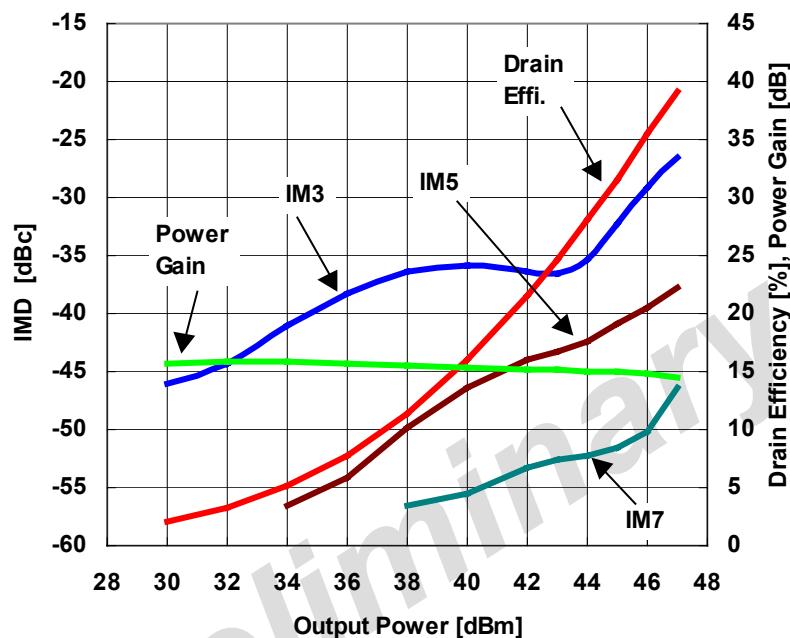


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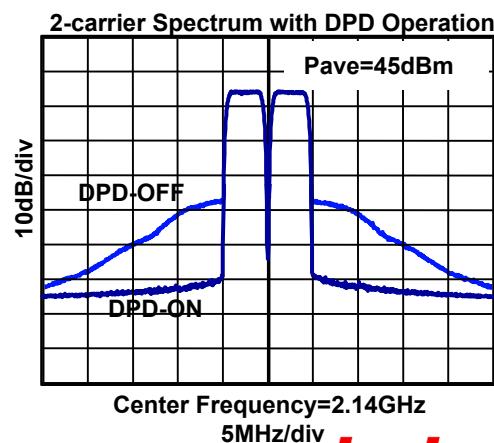
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High Voltage - High Power GaN-HEMT

2-Carrier IMD, Drain Efficiency and Power Gain vs. Output Power
 $V_{DS}=50V$, $I_{DS}=1.0A$, $f_1=2.135GHz$, $f_2=2.145GHz$ (10MHz Spacing)
 Peak/Avg. = 8.5dB@0.01% Probability(CCDF)



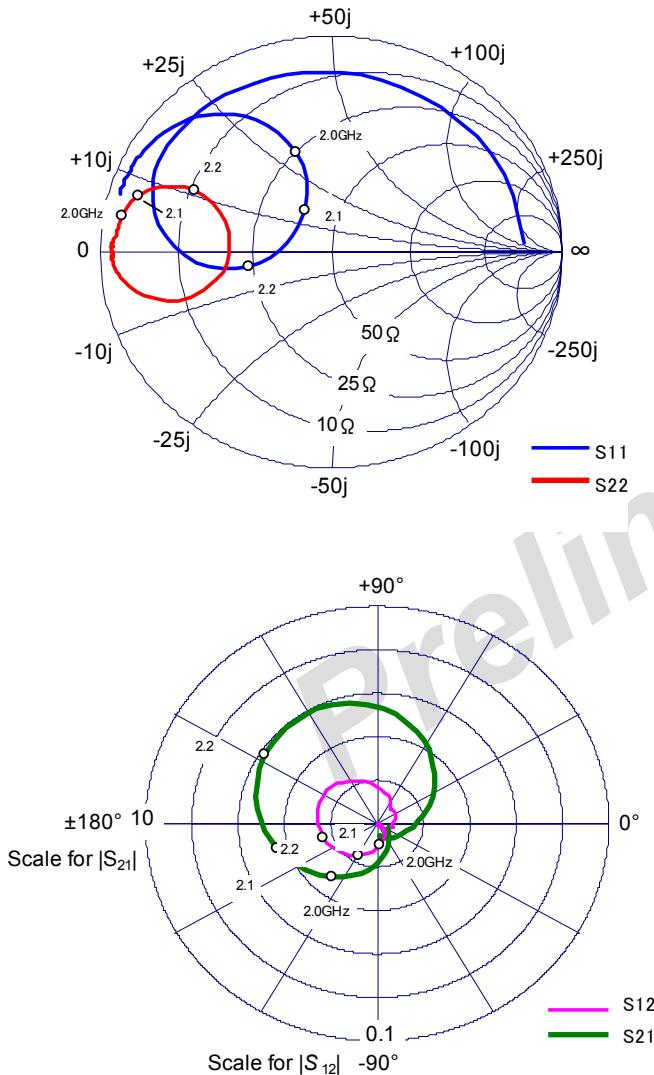
2-Carrier ACLR, Drain Efficiency and Power Gain vs. Output Power with DPD Operation (note
 $V_{DS}=50V$, $I_{DS}=1.0A$
 $f_1=2.1375GHz$, $f_2=2.1425GHz$ (5MHz Spacing)
 Peak/Avg. = 6.5dB@0.01% Probability(CCDF);
 Single Carrier Signal
 Note) Digital Predistortion evaluation test system:
 PMC-Sierra PALADIN-15 DPD chip-set



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S-Parameters @V_{DS}=50V, I_{DS}=1.0A, f=1 to 3 GHz,
Z_I = Z_S = 50 ohm



Freq [GHz]	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.00	0.950	163.5	0.506	-14.4	0.001	-37.4	0.940	-178.3
1.10	0.950	161.1	0.495	-19.4	0.001	-8.8	0.943	-179.3
1.20	0.951	158.1	0.507	-24.5	0.001	-19.5	0.944	179.9
1.30	0.950	155.2	0.539	-30.1	0.001	-53.7	0.945	178.7
1.40	0.941	151.7	0.598	-36.8	0.001	-40.4	0.947	178.0
1.50	0.930	147.6	0.696	-43.7	0.001	-17.3	0.943	177.1
1.60	0.908	142.4	0.849	-52.7	0.001	-32.0	0.941	176.2
1.70	0.876	136.3	1.102	-64.1	0.002	-34.4	0.931	175.2
1.80	0.814	128.2	1.508	-79.2	0.004	-38.3	0.933	173.8
1.90	0.694	118.0	2.156	-99.7	0.006	-57.1	0.925	172.4
2.00	0.489	108.2	3.135	-128.0	0.010	-81.7	0.916	169.3
2.10	0.224	121.0	4.441	-164.8	0.017	-118.2	0.872	162.4
2.11	0.204	127.2	4.579	-169.0	0.017	-122.3	0.859	161.8
2.12	0.188	135.9	4.728	-173.3	0.018	-126.6	0.848	160.6
2.13	0.180	146.1	4.881	-177.6	0.019	-131.0	0.829	160.0
2.14	0.183	156.7	5.015	-177.7	0.019	-135.6	0.814	158.9
2.15	0.196	167.0	5.168	-173.0	0.020	-140.1	0.796	158.0
2.16	0.215	175.5	5.305	-168.0	0.022	-144.4	0.777	157.1
2.17	0.243	-178.1	5.442	-163.0	0.022	-150.2	0.750	156.1
2.18	0.277	-173.5	5.569	-157.8	0.023	-154.4	0.721	155.3
2.19	0.318	-170.9	5.692	-152.3	0.024	-159.1	0.690	154.9
2.20	0.360	-169.4	5.820	-146.6	0.024	-164.8	0.656	154.5
2.30	0.760	170.4	5.331	87.3	0.026	138.3	0.453	-173.8
2.40	0.861	145.0	3.406	42.4	0.019	98.7	0.699	-161.4
2.50	0.862	126.3	2.183	14.7	0.014	75.5	0.837	-166.0
2.60	0.845	108.0	1.551	-6.1	0.011	57.6	0.889	-169.7
2.70	0.831	86.9	1.180	-25.0	0.010	44.1	0.920	-172.7
2.80	0.821	62.1	0.945	-43.3	0.008	21.4	0.935	-175.5
2.90	0.825	33.0	0.761	-62.7	0.007	7.5	0.943	-177.2
3.00	0.836	3.1	0.597	-80.7	0.007	-12.2	0.949	-179.1